



#### SINGLE 2 INPUT POSITIVE NOR GATE

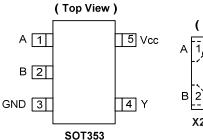
### **Description**

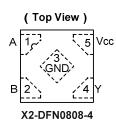
The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

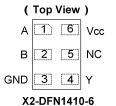
The 74AUP1G02 is a single, two-input, positive NOR gate with a standard push-pull output designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing damaging current backflow when the device is powered down. The gate performs the positive Boolean function:

$$Y = \overline{A + B}$$
 or  $Y = \overline{A} \cdot \overline{B}$ 

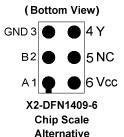
### **Pin Assignments**

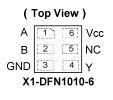












Packages not to scale

#### **Features**

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption

 $I_{CC} < 0.9 \mu A$ 

Low Dynamic Power Consumption

C<sub>PD</sub> = 6.4pF (Typical at 3.6V)

- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250 mV at Vcc = 3.0V.
- I<sub>OFF</sub> Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22

2000-V Human Body Model (A114)

Exceeds 1000-V Charged Device Model (C101)

- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages Named per JESD30E
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

## **Applications**

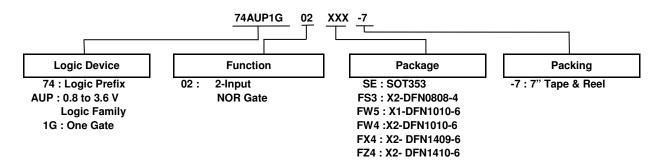
- Suited for Battery and Low Power Needs
- Wide array of products such as:
  - Tablets, E-readers
  - Cell Phones, Personal Navigation / GPS
  - MP3 Players, Cameras, Video Recorders
  - PCs, Ultrabooks, Notebooks, Netbooks
  - Computer Peripherals, Hard Drives, SSDs CD/DVD ROMs
  - TVs, DVDs, DVRs, Set-Top Boxes

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



### **Ordering Information**



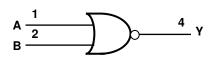
Davisa	Package	Package	Package	7" Tape and Reel		
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix	
74AUP1G02SE-7	SE	SOT353	2.0mm x 2.0mm x 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7	
74AUP1G02FS3-7	FS3	X2-DFN0808-4	0.8mm x 0.8mm x 0.35mm 0.5 mm pad pitch (diamond)	5,000/Tape & Reel	-7	
74AUP1G02FW5-7	FW5	X1-DFN1010-6	1.0mm x 1.0mm x 0.5mm 0.35 mm pad pitch	5,000/Tape & Reel	-7	
74AUP1G02FW4-7	FW4	X2-DFN1010-6	1.0mm x 1.0mm x 0.4mm 0.35 mm pad pitch	5,000/Tape & Reel	-7	
74AUP1G02FX4-7	FX4	X2-DFN1409-6 Chip Scale Alternative	1.4mm x 0.9mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7	
74AUP1G02FZ4-7	FZ4	X2-DFN1410-6	1.4mm x 1.0mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7	

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

## **Pin Descriptions**

Pin Name	Function
Α	Data Input
В	Data Input
GND	Ground
Υ	Data Output
V <sub>CC</sub>	Supply Voltage

# **Logic Diagram**



### **Function Table**

Inp	Inputs					
Α	В	Υ				
L	L	Н				
L	Н	L				
Н	L	L				
Н	Н	L				

<sup>5.</sup> The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.



### **Absolute Maximum Ratings** (Notes 6 & 7) (@T<sub>A</sub> = +25 ℃, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V <sub>CC</sub>	Supply Voltage Range	-0.5 to +4.6	V
$V_{l}$	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> < 0	50	mA
lok	Output Clamp Current (V <sub>O</sub> < 0 )	50	mA
Io	Continuous Output Current (V <sub>O</sub> = 0 to V <sub>CC</sub> )	±20	mA
Icc	Continuous Current through V <sub>CC</sub>	50	mA
$I_{GND}$	Continuous Current through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	℃
T <sub>STG</sub>	Storage Temperature	-65 to +150	℃

Notes

## Recommended Operating Conditions (Note 8) (@T<sub>A</sub> = +25 ℃, unless otherwise specified.)

Symbol	Parar	meter	Min	Max	Unit
V <sub>CC</sub>	Operating Voltage		0.8	3.6	V
$V_{I}$	Input Voltage		0	3.6	V
Vo	Output Voltage		0	$V_{CC}$	V
		$V_{CC} = 0.8V$	_	-20	μΑ
		$V_{CC} = 1.1V$	_	-1.1	
	High Loyal Output Current	$V_{CC} = 1.4V$	_	-1.7	
I <sub>OH</sub>	High-Level Output Current	V <sub>CC</sub> = 1.65V	_	-1.9	mA
		$V_{CC} = 2.3V$	_	-3.1	
		$V_{CC} = 3.0V$	_	-4	
		$V_{CC} = 0.8V$	_	20	μΑ
		$V_{CC} = 1.1V$	_	1.1	
	Low Lovel Output Current	$V_{CC} = 1.4V$	_	1.7	
loL	Low-Level Output Current	$V_{CC} = 1.65V$	_	1.9	mA
		$V_{CC} = 2.3V$	_	3.1	
		$V_{CC} = 3.0V$	_	4	
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 0.8V \text{ to } 3.6V$	_	200	ns/V
T <sub>A</sub>	Operating Free-	Air Temperature	-40	+125	℃

Note:

8. Unused inputs should be held at  $V_{\text{CC}}$  or Ground.

<sup>6.</sup> Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

<sup>7.</sup> Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



# **Electrical Characteristics**(@T<sub>A</sub> = +25 ℃, unless otherwise specified.)

Symbol	Parameter	Test Conditions	V	T <sub>A</sub> = 4	-25°C	T <sub>A</sub> = -40 ℃	to +85℃	Unit
Syllibol	Parameter	rest Conditions	V <sub>CC</sub>	Min	Max	Min	Max	Unit
		_	0.8V to 1.65V	0.80 x V <sub>CC</sub>	_	0.80 x V <sub>CC</sub>	_	
V	High-Level Input	_	1.65V to 1.95V	0.65 x V <sub>CC</sub>	_	0.65 x V <sub>CC</sub>	_	v
V <sub>IH</sub>	Voltage	_	2.3V to 2.7V	1.6	_	1.6	_	, v
		_	3.0 V to 3.6V	2.0	_	2.0	_	
		_	0.8V to 1.65V	_	0.30 x V <sub>CC</sub>	_	0.30 x V <sub>CC</sub>	
VIL	Low-Level Input	_	1.65V to 1.95V	_	0.35 x V <sub>CC</sub>	_	0.35 x V <sub>CC</sub>	v
VIL	Voltage	_	2.3V to 2.7V	_	0.7	_	0.7	, v
		_	3.0V to 3.6V	_	0.9	_	0.9	
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V <sub>CC</sub> - 0.1	_	V <sub>CC</sub> - 0.1	_	
		I <sub>OH</sub> = -1.1mA	1.1V	0.75 x V <sub>CC</sub>	_	0.7 x V <sub>CC</sub>	_	
		I <sub>OH</sub> = -1.7mA	1.4V	1.11	_	1.03	_	
.,	High-Level Output	I <sub>OH</sub> = -1.9mA	1.65V	1.32	_	1.3	_	.,
VoH Voltage	I <sub>OH</sub> = -2.3mA	0.01/	2.05	_	1.97	_	V	
	I <sub>OH</sub> = -3.1mA	2.3V	1.9	_	1.85	_		
		I <sub>OH</sub> = -2.7mA	2) /	2.72	_	2.67	_	-
		I <sub>OH</sub> = -4mA	3V	2.6	_	2.55	_	
		I <sub>OL</sub> = 20μA	0.8V to 3.6V	_	0.1	_	0.1	
		I <sub>OL</sub> = 1.1mA	1.1V	_	0.3 x V <sub>CC</sub>	_	0.3 x V <sub>CC</sub>	
		I <sub>OL</sub> = 1.7mA	1.4V	_	0.31	_	0.37	
	Low-Level Output	I <sub>OL</sub> = 1.9mA	1.65V	_	0.31	_	0.35	1
V <sub>OL</sub>	Voltage	I <sub>OL</sub> = 2.3mA		_	0.31	_	0.33	V
		I <sub>OL</sub> = 3.1mA	2.3V	_	0.44	_	0.45	
		$I_{OL} = 2.7 \text{mA}$		_	0.31	_	0.33	
		I <sub>OL</sub> = 4 mA	3V	_	0.44	_	0.45	
II	Input Current	A or B Input V <sub>I</sub> = GND to 3.6V	0 to 3.6V	_	± 0.1	_	± 0.5	μΑ
I <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 = 0V$ to 3.6V	0	_	0.2	_	0.6	μΑ
Δl <sub>OFF</sub>	Delta Power Down Leakage Current	$V_I$ or $V_O = 0V$ to 3.6V	0V to 0.2V	_	0.2	_	0.6	μΑ
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	0.5	_	0.9	μA
Δl <sub>CC</sub>	Additional Supply Current	One Input at V <sub>CC</sub> -0.6V Other Inputs at V <sub>CC</sub> or GND	3.3V	_	40	_	50	μА



# **Electrical Characteristics** (continued) (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	V	T <sub>A</sub> = -40 ℃	to +125℃	Unit
Syllibol	Parameter	rest Conditions	Vcc	Min	Max	Unit
		_	0.8V to 1.65V	0.80 x V <sub>CC</sub>	_	
V <sub>IH</sub>	High-Level Input	_	1.65V to 1.95V	0.70 x V <sub>CC</sub>	_	v
VIH	Voltage	_	2.3V to 2.7V	1.6	_	_ v
		_	3.0V to 3.6V	2.0		
			0.8V to 1.65V	_	0.25 x V <sub>CC</sub>	
VIL	Low-Level Input	_	1.65V to 1.95V	_	0.30 x V <sub>CC</sub>	V
VIL	Voltage	_	2.3V to 2.7V	_	0.7	v
		_	3.0V to 3.6V	_	0.9	
		$I_{OH} = -20 \mu A$	0.8V to 3.6V	V <sub>CC</sub> – 0.11	_	
		I <sub>OH</sub> = -1.1 mA	1.1V	0.6 x V <sub>CC</sub>	_	
		I <sub>OH</sub> = -1.7 mA	1.4V	0.93	_	
.,	High-Level Output	I <sub>OH</sub> = -1.9 mA	1.65V	1.17	_	
VoH	Voltage	I <sub>OH</sub> = -2.3 mA	0.01/	1.77	_	_ v
		I <sub>OH</sub> = -3.1 mA	2.3V	1.67		
		I <sub>OH</sub> = -2.7 mA	_,,	2.40	_	
		I <sub>OH</sub> = -4 mA	3V	2.30	_	
		I <sub>OL</sub> = 20 μA	0.8V to 3.6V	_	0.11	
		I <sub>OL</sub> = 1.1 mA	1.1V	_	0.33 x V <sub>CC</sub>	
		I <sub>OL</sub> = 1.7 mA	1.4V	_	0.41	
.,	Low-Level Output	I <sub>OL</sub> = 1.9 mA	1.65V	_	0.39	
$V_{OL}$	Voltage	I <sub>OL</sub> = 2.3 mA	0.01/	_	0.36	_ v
		I <sub>OL</sub> = 3.1 mA	2.3V	_	0.50	
		I <sub>OL</sub> = 2.7 mA	01/	_	0.36	
		I <sub>OL</sub> = 4 mA	3V	_	0.50	
II	Input Current	A or B Input V <sub>I</sub> =GND to 3.6V	0 to 3.6V	_	± 0.75	μΑ
loff	Power Down Leakage Current	$V_I$ or $V_O = 0V$ to 3.6V	0	_	± 3.5	μA
Δl <sub>OFF</sub>	Delta Power Down Leakage Current	$V_I$ or $V_O = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μΑ
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	3.0	μA
ΔI <sub>CC</sub>	Additional Supply Current	Input at V <sub>CC</sub> -0.6V Other Inputs at V <sub>CC</sub> or GND	3.3V	_	75	μA



# **Switching Characteristics**

 $C_L = 5pF$ , See Figure 1

Parameter	From Input	TO OUTPUT	Vcc	Т	T <sub>A</sub> = +25 °C		T <sub>A</sub> = -40 °C to +85 °C		T <sub>A</sub> = -40 °C to +125 °C		Unit
Farailletei			VCC	Min	Тур	Max	Min	Max	Min	Max	UIIIL
			0.8V	_	17.0	_	_	_	_	_	
		A or B Y	1.2V ± 0.1V	2.5	5.1	10.8	2.1	12.1	2.1	13.4	
	A or P		1.5V ± 0.1V	1.6	3.7	6.7	1.4	7.8	1.4	8.6	
t <sub>pd</sub>	AUID		1.8V ± 0.15V	1.3	3.0	5.3	1.1	6.2	1.1	6.9	ns
			2.5V ± 0.2V	1.0	2.4	3.9	0.9	4.6	0.9	5.1	
			3.3V ± 0.3V	1.0	2.2	3.4	0.8	4.0	0.8	4.4	

C<sub>L</sub> = 10pF, See Figure 1

Parameter	From Input	To Output	V	1	T <sub>A</sub> = +25 ℃		T <sub>A</sub> = -40 °C to +85 °C		T <sub>A</sub> = -40 °C to +125 °C		Unit
			V <sub>cc</sub>	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	20.4	_	_	_	_	_	
		Y	1.2V ± 0.1V	2.4	6.0	12.8	2.2	14.3	2.2	15.8	
	A or B		1.5V ± 0.1V	1.9	4.3	7.9	1.7	9.2	1.7	10.2	ns
t <sub>pd</sub>	AOID		1.8V ± 0.15V	1.6	3.6	6.2	1.5	7.3	1.5	8.1	
			2.5V ± 0.2V	1.4	3.0	4.7	1.2	5.6	1.2	6.2	
			3.3 V ± 0.3V	1.3	2.7	4.2	1.2	5.0	1.2	5.5	

C<sub>L</sub> = 15pF, See Figure 1

Parameter	From	To Output	V	T <sub>A</sub> = +25 ℃		T <sub>A</sub> = -40 °C to +85 °C		T <sub>A</sub> = -40 °C to +125 °C		Unit	
	Input		V <sub>CC</sub>	Min	Тур	Max	Min	Max	Min	Max	Oiiii
			0.8V	_	23.9	_	_	_	_	_	
		Y	1.2V ± 0.1V	3.4	6.8	14.6	3.1	16.4	3.1	18.1	ns
	A or B		1.5V ± 0.1V	2.3	4.8	8.9	2.0	10.4	2.0	11.5	
t <sub>pd</sub>	AOIB		1.8V ± 0.15V	1.9	4.0	7.0	1.7	8.3	1.7	9.2	
		2.5V ± 0.2V	1.7	3.4	5.4	1.5	6.3	1.5	7.0		
			$3.3V \pm 0.3V$	1.6	3.2	4.8	1.4	5.7	1.4	6.3	

C<sub>L</sub> = 30pF, See Figure 1

Parameter	From Input	To Output	V	Т	T <sub>A</sub> = +25 °C		T <sub>A</sub> = -40 °C to +85 °C		T <sub>A</sub> = -40 °C to +125 °C		Unit
Farailleter			Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	34.2	_	_	_	_	_	
		Y	1.2V ± 0.1V	4.6	19.0	22.0	4.1	22.4	4.1	24.7	
	A or B		1.5V ± 0.1V	3.4	6.4	11.8	2.9	13.9	2.9	15.3	]
t <sub>pd</sub>	AUID		1.8V ± 0.15V	2.6	5.3	9.3	2.3.	11.1	2.3.	12.3	ns
			2.5V ± 0.2V	2.4	4.5	7.1	2.1	8.5	2.1	9.4	1
			$3.3V \pm 0.3V$	2.0	2.9	6.4	2.1	7.7	2.1	8.5	



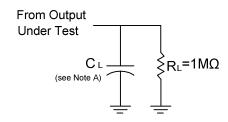
# Operating and Package Characteristics (@T<sub>A</sub> = +25 ℃, unless otherwise specified.)

	Parameter	Test Conditio	ons	V <sub>cc</sub>	Тур	Unit
				0.8V	6.8	
				1.2V ± 0.1V	6.7	
	Power Dissipation	f = 1MH	lz	1.5V ± 0.1V	6.6	
$C_{\sf pd}$	Capacitance	No Loa	d	1.8V ± 0.15V	6.2	pF
				2.5V ± 0.2V	6.5	
				3.3V ± 0.3V	6.4	
Ci	Input Capacitance	$V_i = V_{CC}$ or GND		0V or 3.3V	1.5	pF
		SOT353		_	371	
		X2-DFN0808-4		_	430	
	Thermal Resistance	X1-DFN1010-6	(NI-+- O)	_	435	00.444
θJA	Junction-to-Ambient	X2-DFN1010-6	(Note 9)	_	445	- ℃/W
		X2-DFN1409-6	1	_	470	
		X2-DFN1410-6		_	460	
		SOT353		_	143	
		X2-DFN0808-4	1	_	240	
0	Thermal Resistance	X1-DFN1010-6	(Nata 0)	_	250	00.444
θJC	θ <sub>JC</sub> Junction-to-Case	X2-DFN1010-6	(Note 9)	_	250	- ℃/W
		X2-DFN1409-6		_	275	
		X2-DFN1410-6		_	265	

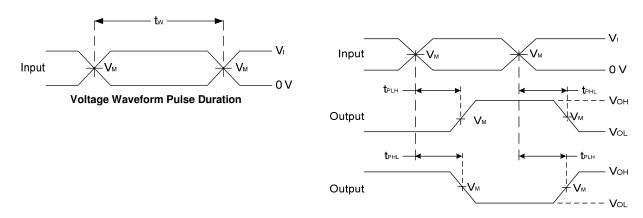
Note: 9. Test condition for each of the six package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



### **Parameter Measurement Information**



Vac	Inputs		V	
Vcc	VI	t <sub>r</sub> /t <sub>f</sub>	- V <sub>M</sub>	CL
0.8V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	5, 10, 15, 30pF
1.2V±0.1V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	5, 10, 15, 30pF
1.5V±0.1V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	5, 10, 15, 30pF
1.8V ±0.15V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	5, 10, 15, 30pF
2.5V±0.2V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	5, 10, 15, 30pF
3.3V±0.3V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	5, 10, 15, 30pF



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10MHz.
  C. Inputs are measured separately one transition per measurement.
- D.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD.}$



### **Marking Information**

(1) SOT353

#### (Top View)

4 XX Y W X3 2

XX: Identification code

Y: Year 0~9

 $\underline{W}$ : Week : A $^{\sim}$ Z : 1 $^{\sim}$ 26 week;

a~z: 27~52 week; z represents 52 and 53 week

X: A~Z: Internal code

Part Number	Package	Identification Code	
74AUP1G02SE-7	SOT353	XJ	

#### (2) X2-DFN0808-4, X1-DFN1010-6, X2-DFN1010-6, X2-DFN1409-6 and X2-DFN1410-6

#### (Top View)

<u>XX</u>  $\underline{Y}\underline{W}\underline{X}$  XX: Identification Code

<u>Y</u> : Year : 0~9

 $\overline{W}$ : Week: A~Z: 1~26 week;

a~z : 27~52 week; z represents 52 and 53 week

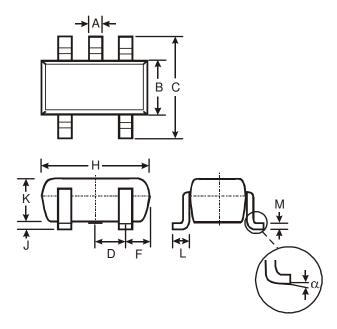
 $\underline{X}$ : A~Z: Internal code

Part Number	Package	Identification Code
74AUP1G02FS3-7	X2-DFN0808-4	YP
74AUP1G02FW5-7	X1-DFN1010-6	Q3
74AUP1G02FW4-7	X2-DFN1010-6	XJ
74AUP1G02FX4-7	X2-DFN1409-6	НВ
74AUP1G02FZ4-7	X2-DFN1410-6	XJ

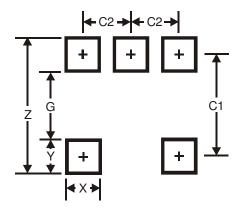


## SOT353 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT353				
Dim	Min	Max	Тур		
Α	0.10	0.30	0.25		
В	1.15	1.35	1.30		
С	2.00	2.20	2.10		
D		0.65 Typ	כ		
F	0.40	0.45	0.425		
Н	1.80	2.20	2.15		
J	0	0.10	0.05		
K	0.90	1.00	1.00		
L	0.25	0.40	0.30		
М	0.10	0.22	0.11		
α	0°	8°	-		
A	All Dimensions in mm				

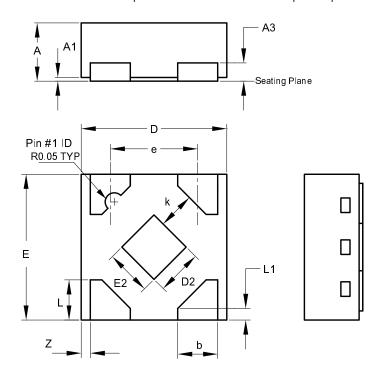


Dimensions	Value (in mm)	
Z	2.5	
G	1.3	
Х	0.42	
Υ	0.6	
C1	1.9	
C2	0.65	

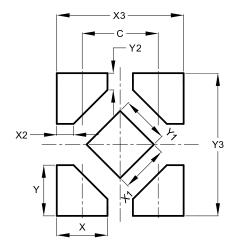


# X2-DFN0808-4 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	X2-DFN0808-4				
Dim	Min	Max	Тур		
Α	0.25	0.35	0.30		
A1	0	0.04	0.02		
A3	-	-	0.13		
b	0.17	0.27	0.22		
D	0.75	0.85	0.80		
D2	0.15	0.35	0.25		
E	0.75	0.85	0.80		
E2	0.15	0.35	0.25		
е	-	-	0.48		
k	0.20	-	-		
L	0.17	0.27	0.22		
L1	0.02	0.12	0.07		
Z	-	-	0.05		
All Dimensions in mm					

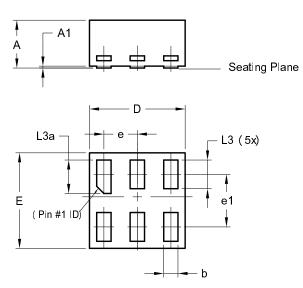


Dimensions	Value
С	0.480
Х	0.320
X1	0.300
X2	0.106
Х3	0.800
Υ	0.320
Y1	0.300
Y2	0.106
Y3	0.900

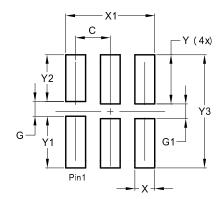


# X1-DFN1010-6 (Type B) Package Outline Dimensions and Suggested Pad Layout

 $Please see AP02002 \ at \ http://www.diodes.com/datasheets/ap02002.pdf \ for \ the \ latest \ version.$ 



	X1-DFN1010-6 (Type B)				
Dim	Min	Max	Тур		
Α	-	0.50	0.39		
A1	-	0.04	-		
b	0.12	0.20	0.15		
D	0.95	1.050	1.00		
Е	0.95	1.050	1.00		
е	e 0.35 BSC				
e1		0.55 B	SC		
L3	0.27	0.30	0.30		
L3a	0.32	0.40	0.35		
All	All Dimensions in mm				

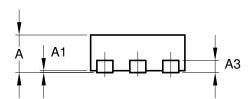


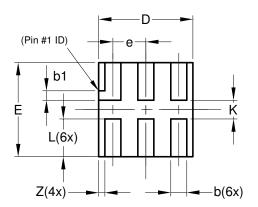
Dimensions	Value	
Dillielisions	(in mm)	
С	0.350	
G	0.150	
G1	0.150	
Х	0.200	
X1	0.900	
Υ	0.500	
Y1	0.525	
Y2	0.475	
Y3	1.150	



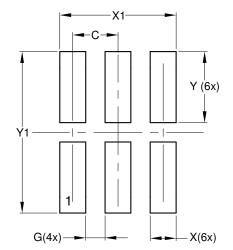
# X2-DFN1010-6 Package Outline Dimensions and Suggested Pad Layout

 $Please see AP02002 \ at \ http://www.diodes.com/datasheets/ap02002.pdf \ for \ the \ latest \ version.$ 





X2-DFN1010-6				
Dim	Min	Max	Тур	
Α	_	0.40	0.39	
<b>A</b> 1	0.00	0.05	0.02	
<b>A3</b>	_		0.13	
b	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
е	_		0.35	
L	0.35	0.45	0.40	
K	0.15	_		
Z	_		0.065	
All Dimensions in mm				

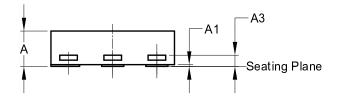


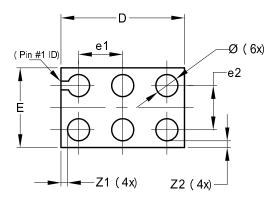
Dimensions	Value (in mm)	
С	0.350	
G	0.150	
X	0.200	
X1	0.900	
Y	0.550	
<b>Y</b> 1	1.250	



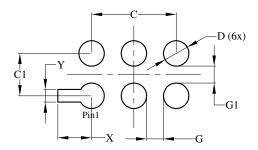
# X2-DFN1409-6 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.





X2-DFN1409-6				
Dim	Min	Max	Тур	
Α	-	0.40	0.39	
<b>A</b> 1	0	0.05	0.02	
A3	-	-	0.13	
Ø	0.20	0.30	0.25	
D	1.35	1.45	1.40	
Е	0.85	0.95	0.90	
e1	-	1	0.50	
e2	-	-	0.50	
<b>Z</b> 1	-	-	0.075	
<b>Z2</b>	-	-	0.075	
All Dimensions in mm				

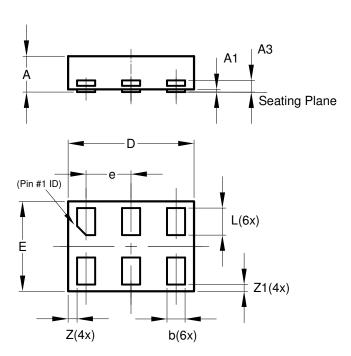


Dimensions	Value (in mm)
С	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
Х	0.400
Υ	0.150

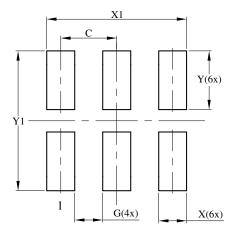


## X2-DFN1410-6 Package Outline Dimensions and Suggested Pad Layout

 $Please see AP02002 \ at \ http://www.diodes.com/datasheets/ap02002.pdf \ for \ the \ latest \ version.$ 



X2-DFN1410-6				
Dim	Min	Max	Тур	
Α	_	0.40	0.39	
<b>A</b> 1	0.00	0.05	0.02	
A3	_		0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е			0.50	
L	0.25	0.35	0.30	
Z	_		0.10	
<b>Z</b> 1	0.045	0.105	0.075	
All Dimensions in mm				



Dimensions	Value (in mm)
С	0.500
G	0.250
X	0.250
X1	1.250
Υ	0.525
<b>Y</b> 1	1.250



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